

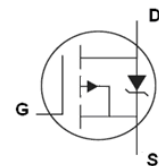
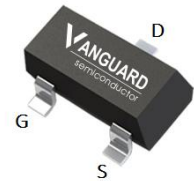
Features

- P-Channel
- Enhancement mode
- Fast Switching
- Pb-free lead plating; RoHS compliant

V_{DS}	-20	V
$R_{DS(on),TYP} @ V_{GS}=-4.5V$	77	mΩ
$R_{DS(on),TYP} @ V_{GS}=-3.3V$	87	mΩ
$R_{DS(on),TYP} @ V_{GS}=-2.5V$	103	mΩ
I_D	-3	A



SOT23



Part ID	Package Type	Marking	Tape and reel information
V2301BC	SOT23	A1SHB	3000pcs/reel

Maximum ratings, at $T_A = 25\text{ °C}$, unless otherwise specified

Symbol	Parameter	Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage	-20	V
V_{GS}	Gate-Source voltage	±12	V
I_S	Diode continuous forward current	$T_A = 25\text{ °C}$ -0.83	A
I_D	Continuous drain current @ $V_{GS} = -4.5V$	$T_A = 25\text{ °C}$ -3	A
		$T_A = 70\text{ °C}$ -2.3	A
I_{DM}	Pulse drain current tested ①	$T_A = 25\text{ °C}$ 12	A
P_D	Maximum power dissipation	$T_A = 25\text{ °C}$ 1	W
T_{STG}, T_J	Storage and junction temperature range	-55 to 150	°C
Thermal Characteristics			
$R_{\theta JL}$	Thermal Resistance, Junction-to-Lead	80	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	125	°C/W

Electrical Characteristics

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T_j = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-20	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current(T _j =25°C)	V _{DS} =-20V, V _{GS} =0V	--	--	1	μA
	Zero Gate Voltage Drain Current(T _j =125°C)	V _{DS} =-20V, V _{GS} =0V	--	--	100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±12V, V _{DS} =0V	--	--	±100	nA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.5	--	-1.2	V
R _{DS(ON)}	Drain-Source On-State Resistance②	V _{GS} =-4.5V, I _D =-3A	--	77	115	mΩ
		V _{GS} =-3.3V, I _D =-2A	--	87	130	mΩ
		V _{GS} =-2.5V, I _D =-2A	--	103	190	mΩ
Dynamic Electrical Characteristics @ T_j = 25°C (unless otherwise stated)						
C _{iss}	Input Capacitance	V _{DS} =-10V, V _{GS} =0V, f=1MHz	290	340	390	pF
C _{oss}	Output Capacitance		45	55	65	pF
C _{rss}	Reverse Transfer Capacitance		35	45	55	pF
Q _g	Total Gate Charge	V _{DS} =-10V, I _D =-3A, V _{GS} =-4.5V	--	4.1	--	nC
Q _{gs}	Gate-Source Charge		--	1.6	--	nC
Q _{gd}	Gate-Drain Charge		--	2.1	--	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} =-10 V, I _D =-3A, R _G =3Ω, V _{GS} =-4.5V	--	13	--	ns
t _r	Turn-on Rise Time		--	7.5	--	ns
t _{d(off)}	Turn-Off Delay Time		--	24	--	ns
t _f	Turn-Off Fall Time		--	10	--	ns
Source- Drain Diode Characteristics @ T_j = 25°C (unless otherwise stated)						
V _{SD}	Forward on voltage	I _{SD} =-1.6A, V _{GS} =0V	--	-0.9	-1.2	V
t _{rr}	Reverse Recovery Time	T _j =25°C, I _{sd} =-3A, V _{GS} =0V	--	13	--	ns
Q _{rr}	Reverse Recovery Charge	di/dt=-100A/μs	--	4.3	--	nC

NOTE:

- ① Repetitive rating; pulse width limited by max junction temperature.
 ② Pulse width ≤ 300μs; duty cycles ≤ 2%.

Typical Characteristics

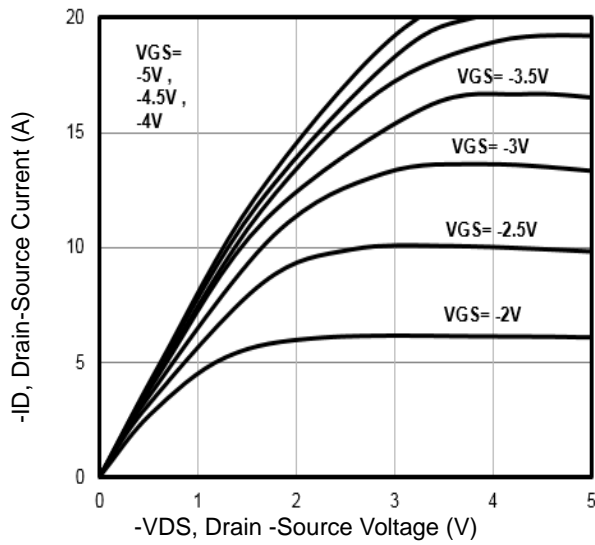


Fig1. Typical Output Characteristics

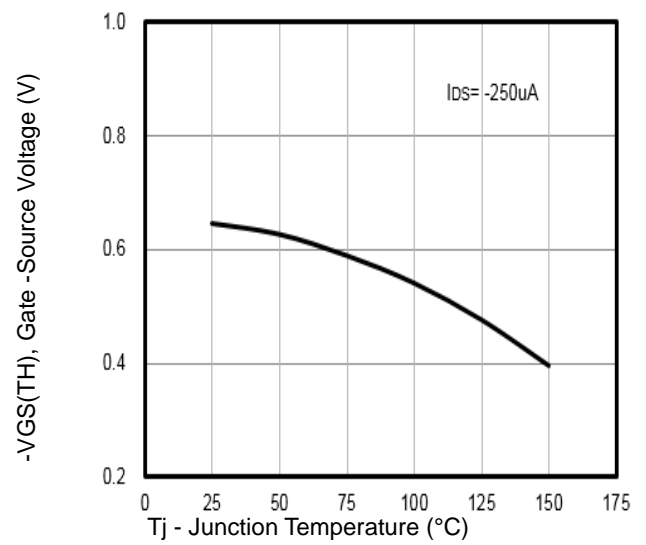


Fig2. -VGS(TH) Gate-Source Voltage Vs. Tj

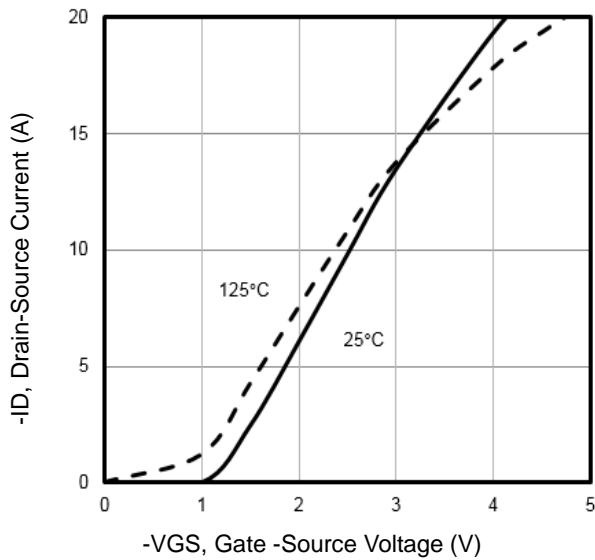


Fig3. Typical Transfer Characteristics

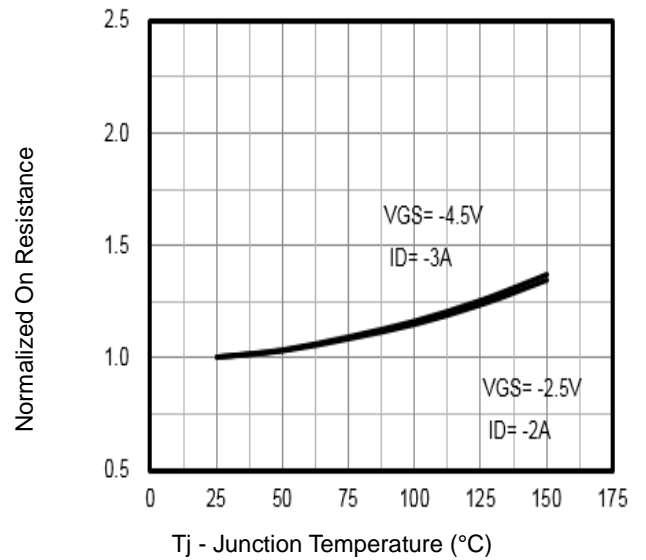


Fig4. Normalized On-Resistance Vs. Tj

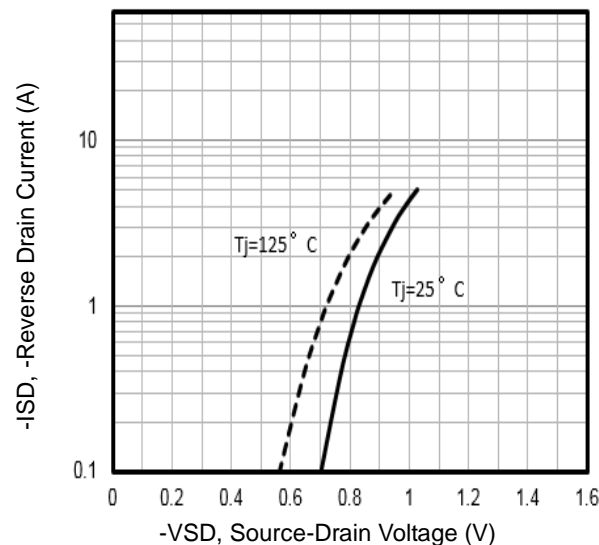


Fig5. Typical Source-Drain Diode Forward Voltage

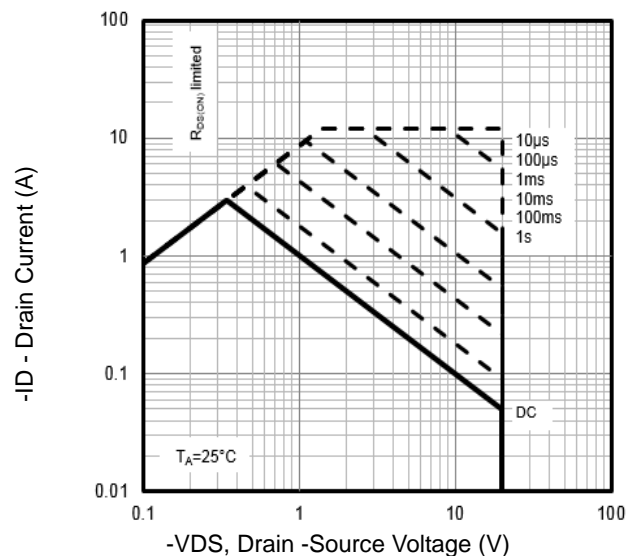


Fig6. Maximum Safe Operating Area

Typical Characteristics

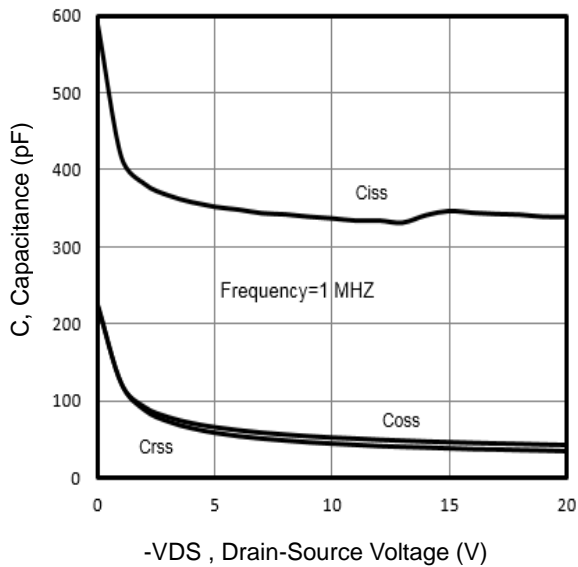


Fig7. Typical Capacitance Vs.Drain-Source Voltage

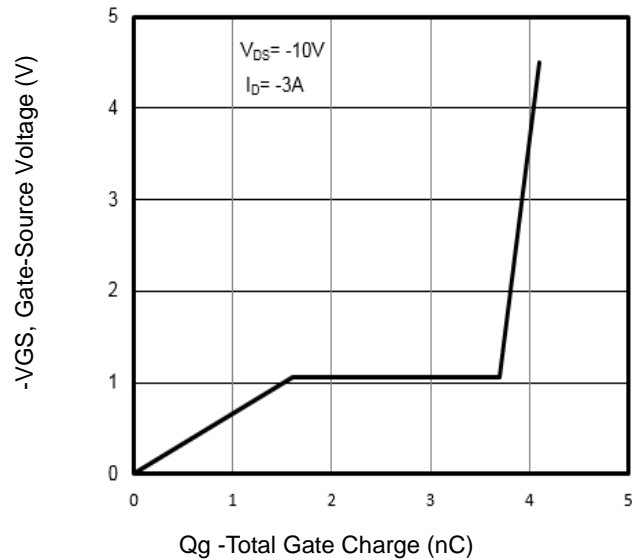


Fig8. Typical Gate Charge Vs.Gate-Source Voltage

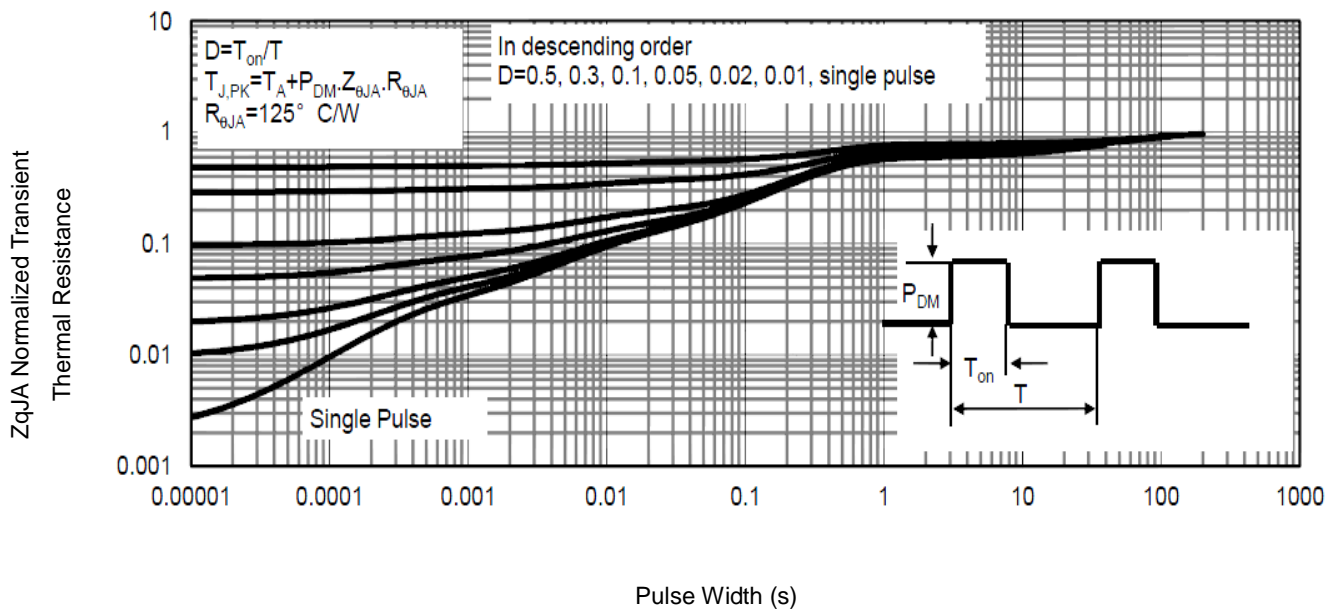


Fig9. Normalized Maximum Transient Thermal Impedance

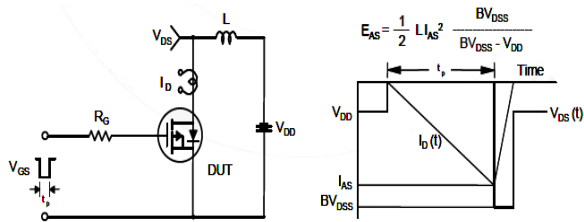


Fig10. Unclamped Inductive Test Circuit and waveforms

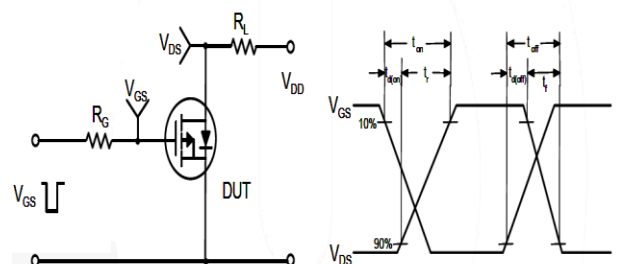
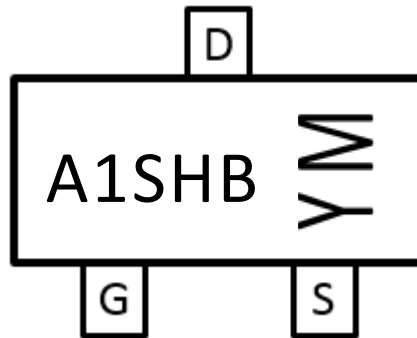


Fig11. Switching Time Test Circuit and waveforms

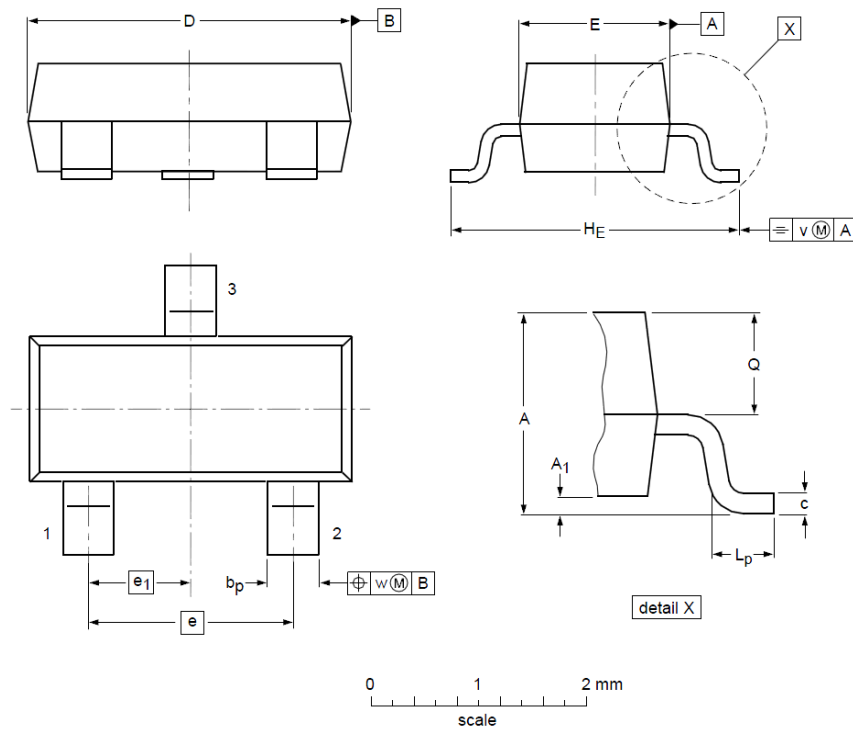
Marking Information



A1SHB: Part Number

YM: Date Code, Y means assembly year, M means assembly month

SOT23 Package Outline Data



Label	DIMENSIONS (unit: mm)		
	Min	Typ	Max
A	0.90	1.03	1.10
A ₁	0.01	0.05	0.10
b _p	0.38	0.42	0.48
c	0.09	0.13	0.15
D	2.80	2.92	3.00
E	1.20	1.33	1.40
e	--	1.90	--
e ₁	--	0.95	--
H _E	2.10	2.40	2.50
L _p	0.40	0.50	0.60
Q	0.45	0.49	0.55
v	--	0.20	--
w	--	0.10	--

Notes:

1. Follow JEDEC TO-236, variation AB.
2. Dimension "D" does NOT include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.25mm per side.
3. Dimension "E" does NOT include interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.25mm per side.

Customer Service

Sales and Service:

sales@vgsemi.com

Vanguard Semiconductor CO., LTD

TEL: (86-755) -26902410

FAX: (86-755) -26907027

WEB: www.vgsemi.com